

60 GHz Wireless in High Energy Physics

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Outline

- Readout Challenges in HEP
- Wireless Data Transmission for HEP
- 60 GHz ASIC
- 3D chip Advantages
- First Experience
- Summary and Outlook



Readout Challenges in HEP

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Readout Challenges in HEP



Readout Challenges in HEP



Readout Challenges in HEP



High Precision Tracking Detectors

- Innermost silicon layers
 - High event rates: f=O(100) MHz
 - High particle fluxes
 - Data rate/area of 10¹⁰ signals/second/cm²
- Outer silicon layers
 - Factor 10-100 smaller particle flux!
 - Data rate/area 10⁸ signals/ second /cm²
 - Wireless multi Gbit/s readout?





Bandwidth Limitations in Inner Detectors



Extra Material from optical / electrical RO

≈1m

Cables run along detector layers: Dead material induced particle scattering

ATLAS UTOPIA Design for High Lumi LHC

Wireless Data Transmission for HEP

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Wireless Readout?



Data Path for Wireless



The 60 GHz Band

- 60 GHz O₂ absorption
- Large damping over 10m
- Unlicensed band 57-66 GHz
- 9 GHz usable
- Multi Gbit/s transfer capacity







Why is the 60 GHz Band so attractive?

- The mm-wave frequency range is very attractive:
 - Data rates and bandwidth are never enough
 - Uncompressed video:
 - High definition multimedia interface (HDMI)(2Gb/s)
 - High speed file transfer among electronic devices
 - Fast movie or video game down load from kiosk



And now the High Energy Physics

Requirements for Wireless in HEP

- High bandwidth
 - o 60 GHz band could offer 5 Gb/s per link
- Low power
 - O(1000) RF interconnects
 - Cooling and power cabling limited
- Low material budget
 - Extra material causes multiple scattering
- High system integration
 - Direct coupling of readout chips to RF system
- Radiation hardness
 - O(MRad) levels in LHC detectors





60 GHz Antenna

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Multiple Wireless Readout

- O(1000) links needed
- ... but only over short (10 cm) distance
- High directivity helps
 - o Limits cross talk
 - Saves power
 - Typically sensor layers are well aligned
- Distance from sensor to RF link is kept small
 - Less material for data lines
 - Better for high speed electrical signals

Application specific integrated circuit (ASIC) necessary!



60 GHz ASIC

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60 GHz Transceiver System

Transmitter

- High power efficiency
- High gain and stability

Receiver

- Low noise amplifier
- Balance gain, linearity and noise
- Low power dissipation



60 GHz Transceiver System

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- High gain and stability

Receiver

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Low Noise Amplifier Issues

- Power dissipation (10 mW)
- Noise Figure (6dB)
- Linearity
- Stability
- Impedance matching
- Power gain (16dB)
- Bandwidth (>10GHz)
- Insensitive to process variation

Hans Kristian Soltveit



Low Noise Amplifier Issues



Characteristics of Low Noise Amplifier



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ASIC Timeline

- Diploma thesis for VCO design: complete
- Full analogue chip design: progressing today well
 - Low noise amplifier
 - Power amplifier
 - Mixer cell / Gilbert cell
 - Band pass filter + antenna
- Missing:
 - Matching between blocks
 - Corner simulation

2011

June 2012

- Wavelengths at 60 GHz: 5mm
- Possible to integrate receive and transmit antenna(s) on-chip
- High directivity is desired:
 - o Better S/N-ratio
 - Reduce power consumption
 - Reduce inter-use interference
- SiGe process (HBT)
 - High dielectric constant in Silicon (11.7)
 - Multiple metal layers on ICs available
 - Can be used to fabricate mm-wave antennas



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⁶⁰ GHz Antenna

Singapore Institute of Manufacturing Technology [2]

- Eliminate cable/connectors loss
- No need for high-frequency electrostatic discharge protection
- Save PCB real estate
- Reduce fabrication costs
- Alternatives:
 - On board antenna
 - Antenna (CMOS) on extra chip (MCP)
 - Antenna (non SiGe) in 3-D stack



60 GHz Antenna

Singapore Institute of Manufacturing Technology [2]

3D Chip Advantages

... for wireless readout chip

3D Chips opens up new Possibilities



- RF signaling does not require direct connection
- Capacitive or inductive coupling for inter-layer transmission
- 3D chips become industry standard
- Other 3D chip projects advancing: ATLAS-FTK AMchip5



Why 3D Stacking?

- 2-D chip layouts \rightarrow 3-D chip stacking
- Increased performance –
 Out scaling Moore's law
- Decreasing system risk
 - 130 nm analog + 65 nm digital
 - ... instead of 65 nm mixed signal SOC.
 - Good for fast serializer (65nm)
 - Good for antenna



First Experience

Current Lab Setups

Starting point

- High end measurement equipment
- Goals:
 - Verification system: Demonstrator
 - o Integration ...
 - ... with commercial ASICs
 - Replace by self made ASIC (blocks) later
 - Fully integrated ASIC



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• Goals:

- Verification system: Demonstrator
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Demonstrator 1/4



Demonstrator 2/4



Demonstrator 3/4

- Demonstrator 60 GHz transmission setup
- Off the shelf components
 - Transmitter: Gotmic TXQ060A01
 - Receiver: Gotmic RXQ060A01
 - Hittite phase-locked oscillator
- Power distribution boxes
 - Many different voltages needed
 - Bias currents need attention
- 68 GHz spectrum analyzer





Demonstrator 4/4

- Reference clock system test (HD)
 - ASIC for 15 GHz reference clock generation
 - Signal quality promising
- Transmission test (Heinrich Hertz Institute):
 - o Transmitter
 - Low gain
 - Broken mixer
 - o Receiver
 - Operation at 1.7 Gbit/s (60 GHz carrier) achieved
 - I_{BIAS} fine tuning
 - External 15 GHz generator for higher sensitivity
 - External reference transmitter system used
 - Binary phase shift keying applied



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N/C

Data Transmission @ 60 GHz

- Data transmitted by modular reference system
- Data receiver in one chip (Gotmic RXQ060A01)
- 1.7 Gbit/s achieved
- Over 2 meters
- Signal quality can be improved ...



Heinrich Hertz Institute





2

symbol

Summary

- The 60 GHz band interesting for Trigger-Tracker at LHC
- mm-wave systems on silicon substrate challenging
 - SiGe HBT technology chosen
 - ASIC design started
- 60 GHz demonstrator reference for future ASIC development
 - 1.7 Gbit/s achieved over 2m



Outlook

- Simulation of multi antenna system in detector environment with ray tracing
- Reference system with full 5 Gbit/s
- Design of full wire less transmission system on chip
- 3D-chip integration



Backup Slides

Data Links in High Energy Physics

- Specialized solution at technology frontier in "difficult" environments
 - High bandwidth
 - Small form factors / low mass
 - Radiation tolerance
 - Specific solutions
 - Prototypes



Detector Readout Model



Readout/Trigger Concepts

- "Traditional Solution"
 - Multi trigger level system with pipelined front end buffers



- "Modern concept"
 - Self-triggered frontends with event buffers for event building



The "First Meter" Bottleneck

Example:

Upgrade ATLAS Barrel Strip Detector as first level trigger

Stave Design



Today's High Speed Interconnects

Optical







Today's High Speed Interconnects

- Km range optical
 - Between data centers and CERN
 - From experiments to CERN data center
- 100 m range optical (copper exceptions
 o From front end electronics to counting house
 o Between counting house levels (rack rows)
- 1 m to 10 m range copper (optical exceptions)
 o Rack to rack
 - Front end boards to repeaters on detector
- cm range copper
 - Board to board
 - Detector to board



Critical Parameters

- The front end readout rate can be characterized by 3 numbers
 - o Gbps / cm²
 - Gbps / g
 - o Gbps/W



New technologies will push these numbers up!

New Approaches



New Approaches

Retolution 1200x1029 (Free Photoshop PSD Re downlos www.peter sphercus



ASIC for 60 GHz Wireless

- Wireless data transfer ...
- ... between silicon sensor layers
- 60 GHz carrier frequency
- O(5)Gb/s per link
- O(1000) links
- Full system on chip approach
 - No external RF components required
 - Little material
 - Little power/cooling
- Radiation hard design



- Millimeter-Wave wavelengths at 60 GHz (5mm)
 - Possible to integrate receive and transmit antenna(s) on-chip
 - High directivity is desired to improve
 - S/N-ratio
 - reduce power consumption
 - reduce inter-use interference
 - SiGe process (HBT)
 - High dielectric constant in Silicon (11.7)
 - Multiple metal layers on ICs available
 - Can be used to fabricate mm-wave antennas
 - Eliminate cable/connectors loss
 - No need for high-frequency electrostatic discharge protection
 - Save PCB real estate
 - Reduce fabrication costs

Low Noise Amplifier Issues

- Power dissipation
- Noise Figure
- Linearity
- Stability
- Impedance matching
- Power gain
- Bandwidth
- Insensitive to process variation



Three Fundamental differences compared to the lower frequency colleague:

- 1. Transistors operate much closer to their cut-off frequency
- 2. Parasitic elements represent a much larger portion of the total impedance
- 3. Signals with small wavelengths results in distributed effects within the circuit

Mixer Issues

- Double-balanced Gilbert cell for LO-RF leakage
- Design strategy: minimize noise, maximize linearity
- CM inductor for noise and headroom
- Middle inductors increase gain and reduce noise



Power Amplifier Issues

- Multi-stage amplifiers
 - Initial stages are optimized for gain
 - Last stage for maximum output power
- Technology
 - Supply voltage
 - o Substrate
 - Breakdown voltage
 - \circ F_t
 - Thermal conductivity

Why 3D Stacking?

- Reducing cost:
 - 3-D integration cheaper than shrinking 2-D design
 - Moving passives onto interposer
- Reduce the size of the overall chip
- Boost the speed between functional blocks
- Uses Through-Silicon Vias (TSV)
 - Vertical connection etched through the silicon wafer
 - Filled with metal
 - No wires between the chips
- Shortens the distance on a chip by 1000 times compared to a 2-D chip wire bonds

Further Applications

Quantum Optics

- Quantum optics has flourished over the last decades
- RF requirements similar to ours
- Multi GHz technology can be used for Rydberg atom stimulation

Plasma Wake Field Acceleration

- Plasma wake field acceleration has been demonstrated
 - Unprecedented acceleration gradients feasible
 - LHC might become driving beam for PWA
- Micro-bunching important for PWA
 - Micro-bunches must be controlled
 - Stimulation
 - Characterization
 - Frequencies lie in the GHz range
 - Radiation hardness requirements and number of RF units similar to HEP detectors

Citation(s)

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Disclaimer

Most slides are based on material shown by André Schöning and Hans Kristian Soltveit during the

1st Detector Readout Link Topical Workshop of the Helmholtz Alliance